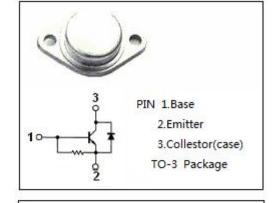


ISC Silicon NPN Power Transistor

2SD1301

DESCRIPTION

- · High Breakdown Voltage-
 - : V_{CBO}= 1500V (Min)
- · High Switching Speed
- · Low Collector Saturation Voltage-
 - : V_{CE(sat)}= 3.0V(Max.)@ I_C= 1A
- · Wide area of safe operation
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

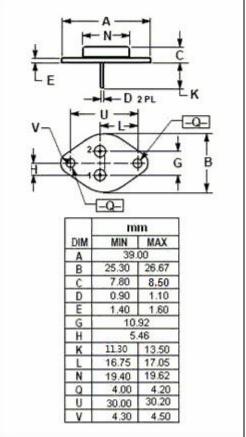


APPLICATIONS

• Designed for color TV horizontal output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1500	V
V _{CES}	Collector- Emitter Voltage(V _{BE} = 0)	1500	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current- Continuous	2	Α
Ісм	Collector Current-Peak	8	Α
Pc	Collector Power Dissipation @ T _C = 25°C	45	W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-65~150	$^{\circ}$





ISC Silicon NPN Power Transistor

2SD1301

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{EBO}	Emitter-Base Breakdown Voltage	I _E = 500mA; I _C = 0	5.0			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1A; I _B = 0.4A			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I _C = 1A; I _B = 0.4A			1.5	V
Ісво	Collector Cutoff Current	V _{CB} = 750V; I _E = 0			50	μ А
		V _{CB} = 1500V; I _E = 0			1	mA
h _{FE}	DC Current Gain	I _C = 1A; V _{CE} = 10V	3		12	
V _{ECF}	C-E Diode Forward Voltage	I _F = 4A			2.5	V
ts	Storage Time	1 - 10 1 - 0 10			6.0	μS
tf	Fall Time	I _C = 1A, I _{Bend} = 0.4A			0.8	μS

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